







#### **DUAL 20V NPN LOW SATURATION SWITCHING TRANSISTOR**

#### **Features and Benefits**

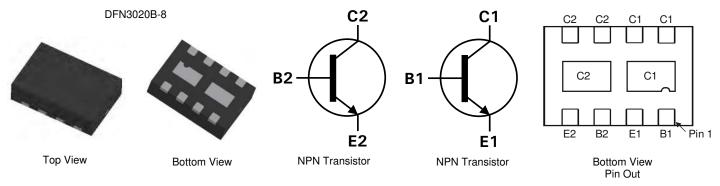
- BV<sub>CEO</sub> > 20V
- I<sub>C</sub> = 4.5A Continuous Collector Current
- Low Saturation Voltage (150mV @ 1A)
- R<sub>SAT</sub> = 47mΩ for a Low Equivalent On-Resistance
- h<sub>FE</sub> specified up to 6A for high current gain hold up
- Dual NPN saving footprint and component count
- Low profile 0.8mm high package for thin applications
- R<sub>B,JA</sub> efficient, 40% lower than SOT26
- 6mm² footprint, 50% smaller than TSOP6 and SOT26
- Lead-Free, RoHS Compliant (Note 1)
- Halogen and Antimony Free. "Green" Device (Note 2)
- Qualified to AEC-Q101 Standards for High Reliability

#### **Mechanical Data**

- Case: DFN3020B-3
- Case material: Molded Plastic. "Green" Molding Compound.
- Terminals: Pre-Plated NiPdAu leadframe.
- UL Flammability Rating 94V-0
- Nominal package height: 0.8mm
- Moisture Sensitivity: Level 1 per J-STD-020
- Weight: 0.013 grams (approximate)

### **Applications**

- DC-DC Converters
- · Charging circuits
- Motor control
- Power switches
- Portable applications



**Equivalent Circuit** 

#### Ordering Information (Note 3)

Product	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
ZXTD618MCTA	DBB	7	8	3,000

Notes:

- 1. No purposefully added lead.
- 2. Diodes Inc's "Green" Policy can be found on our website at http://www.diodes.com
- 3. For Packaging Details, go to our website at http://www.diodes.com.

## **Marking Information**



DBB = Product Type Marking Code Top View, Dot Denotes Pin 1





#### Maximum Ratings @TA = 25°C unless otherwise specified

Parameter	Symbol	Limit	Unit
Collector-Base Voltage	V <sub>CBO</sub>	40	
Collector-Emitter Voltage	V <sub>CEO</sub>	20	V
Emitter-Base Voltage	V <sub>EBO</sub>	7	
Peak Pulse Current	Ісм	12	
Continuous Collector Current (Notes 4 and 7)	Ic	4.5	^
Continuous Collector Current (Notes 5 and 7)	I <sub>C</sub>	5	^
Base Current	I <sub>B</sub>	1	

## Thermal Characteristics @ TA = 25°C unless otherwise specified

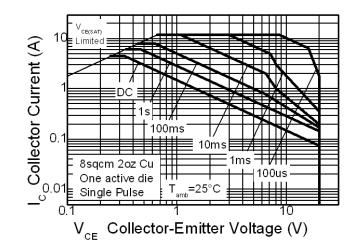
Characteristic	Symbol	Value	Unit		
	(Notes 4 & 7)		1.5 12	W W^°C	
Power Dissipation	(Notes 5 & 7)		2.45 19.6		
Linear Derating Factor	(Notes 6 & 7)	P <sub>D</sub>	1.13 8		
	(Notes 6 & 8)		1.7 13.6		
	(Notes 4 & 7)		83.3		
Thermal Resistance, Junction to Ambient	(Notes 5 & 7)		51.0	°C/W	
mermai Resistance, Junction to Ambient	(Notes 6 & 7)	$R_{\theta JA}$	111		
	(Notes 6 & 8)		73.5		
Thermal Resistance, Junction to Lead	(Notes 7 & 9)	$R_{ heta JL}$	17.1		
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C		

Notes:

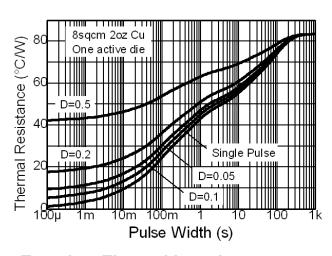
- 4. For a dual device surface mounted on 28mm x 28mm (8cm²) FR4 PCB with high coverage of single sided 2 oz copper, in still air conditions; the device is measured when operating in a steady-state condition. The heatsink is split in half with the exposed collector pads connected to each half.
- 5. Same as note (4), except the device is measured at t <5 sec.
  6. Same as note (4), except the device is surface mounted on 31mm x 31mm (10cm²) FR4 PCB with high coverage of single sided 1oz copper.
- 7. For a dual device with one active die.
- 8. For dual device with 2 active die running at equal power.
- 9. Thermal resistance from junction to solder-point (at the end of the collector lead).



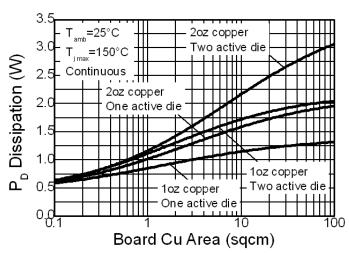
#### **Thermal Characteristics**



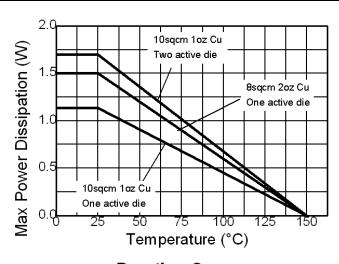
### Safe Operating Area



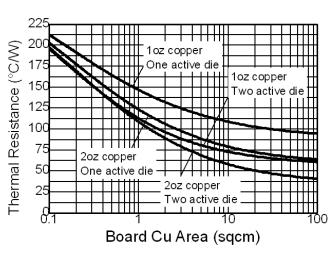
## **Transient Thermal Impedance**



# Power Dissipation v Board Area



## **Derating Curve**



#### Thermal Resistance v Board Area





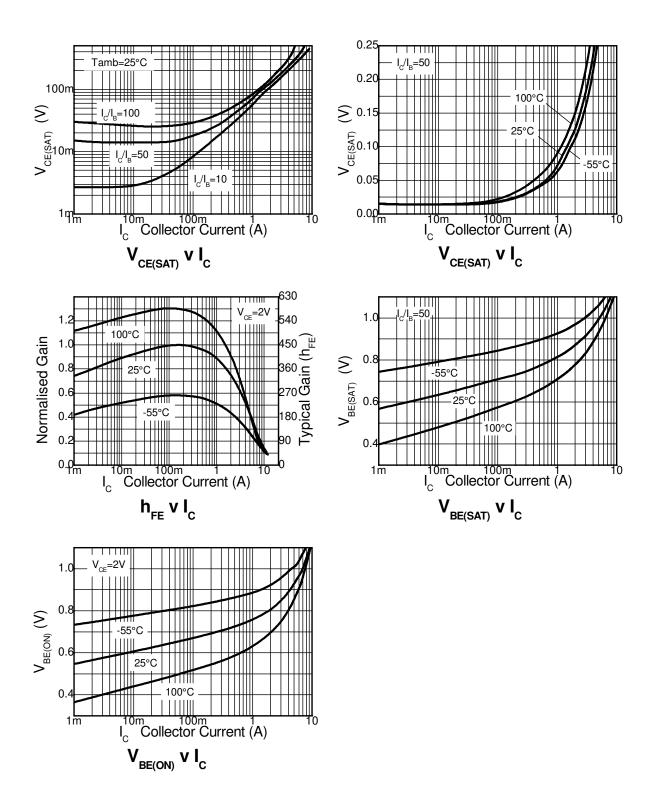
## Electrical Characteristics @TA = 25°C unless otherwise specified

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV <sub>CBO</sub>	40	100	-	V	$I_C = 100\mu A$
Collector-Emitter Breakdown Voltage (Note 10)	BV <sub>CEO</sub>	20	27	-	V	I <sub>C</sub> = 10mA
Emitter-Base Breakdown Voltage	$BV_{EBO}$	7.0	8.2	-	V	$I_E = 100 \mu A$
Collector Cutoff Current	I <sub>CBO</sub>	-	-	100	nA	$V_{CB} = 30V$
Emitter Cutoff Current	I <sub>EBO</sub>	-	-	100	. nA	$V_{EB} = 6V$
Collector Emitter Cutoff Current	I <sub>CES</sub>	-	-	100	nA	V <sub>CES</sub> = 16V
Static Forward Current Transfer Ratio (Note 10)	h <sub>FE</sub>	200 300 200 100	400 450 360 180	- - -	-	$\begin{split} &I_{C} = 10 \text{mA}, \ V_{CE} = 2 \text{V} \\ &I_{C} = 200 \text{mA}, \ V_{CE} = 2 \text{V} \\ &I_{C} = 2 \text{A}, \ V_{CE} = 2 \text{V} \\ &I_{C} = 6 \text{A}, \ V_{CE} = 2 \text{V} \end{split}$
Collector-Emitter Saturation Voltage (Note 10)	V <sub>CE(sat)</sub>	- - -	8 90 115 190 210	15 150 135 250 300	mV	$I_C = 0.1A$ , $I_B = 10mA$ $I_C = 1A$ , $I_B = 10mA$ $I_C = 2A$ , $I_B = 50mA$ $I_C = 3A$ , $I_B = 100mA$ $I_C = 4.5A$ , $I_B = 125mA$
Base-Emitter Turn-On Voltage (Note 10)	V <sub>BE(on)</sub>	-	0.88	0.97	V	I <sub>C</sub> = 4.5A, V <sub>CE</sub> = 2V
Base-Emitter Saturation Voltage (Note 10)	V <sub>BE(sat)</sub>	-	0.98	1.07	V	I <sub>C</sub> = 4.5A, I <sub>B</sub> = 125mA
Output Capacitance	$C_obo$	-	23	30	pF	V <sub>CB</sub> = 10V. f = 1MHz
Transition Frequency	f <sub>T</sub>	100	140	-	MHz	$V_{CE} = 10V, I_{C} = 50mA,$ f = 100MHz
Turn-on Time	t <sub>on</sub>	-	170	-	ns	$V_{CC} = 10V, I_C = 3A$
Turn-off Time	t <sub>off</sub>	-	400	-	ns	$I_{B1} = I_{B2} = 10 \text{mA}$

Notes: 10. Measured under pulsed conditions. Pulse width  $\leq$  300  $\mu$ s. Duty cycle  $\leq$  2%

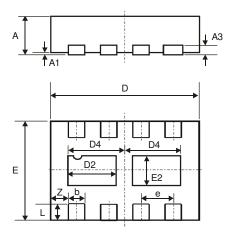


### **Typical Electrical Characteristics**



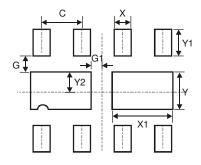


## **Package Outline Dimensions**



DFN3020B-8					
Dim	Min	Max	Тур		
Α	0.77	0.83	0.80		
<b>A</b> 1	0	0.05	0.02		
A3	1	1	0.15		
b	0.25	0.35	0.30		
D	2.95	3.075	3.00		
D2	0.82	1.02	0.92		
D4	1.01	1.21	1.11		
е	-	-	0.65		
Е	1.95	2.075	2.00		
E2	0.43	0.63	0.53		
L	0.25	0.35	0.30		
Z	-	-	0.375		
All Dimensions in mm					

## **Suggested Pad Layout**



Dimensions	Value (in mm)
С	0.650
G	0.285
G1	0.090
X	0.400
X1	1.120
Υ	0.730
Y1	0.500
Y2	0.365





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